

STAC4932F

RF power transistors HF/VHF/UHF N-channel MOSFETs

Preliminary data

Features

- Excellent thermal stability
- Common source push-pull configuration
- P_{OUT} = 1000 W min. (1200 W typ.) with 26 dB gain @ 123 MHz
- Pulse conditions: 1 msec 10%
- In compliance with the 2002/95/EC European directive
- ST air cavity packaging technology STAC[®] package

Description

The STAC4932F is a N-channel MOS field-effect RF power transistor. It is intended for 100 V pulse applications up to 250 MHz. This device is suitable for use in industrial, scientific and medical applications.

The STAC4932B benefits from the latest generation of efficient, patent-pending package technology, otherwise known as STAC®.

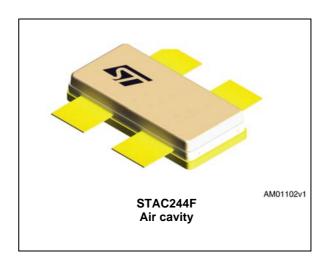


Figure 1. Pin connection

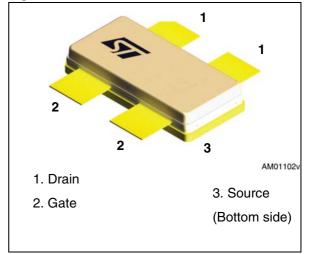


Table 1. Device summary

Order code	Marking	Package	Packaging	
STAC4932F	STAC4932F	STAC244F	Plastic tray	

Contents STAC4932F

Contents

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STAC4932F Electrical data

1 Electrical data

1.1 Maximum ratings

Table 2. Absolute maximum ratings $(T_{CASE} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit
V _{(BR)DSS} ⁽¹⁾	Drain source voltage	200	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 1 M\Omega$)	200	V
V_{GS}	Gate-source voltage	±20	٧
T _J	Max. operating junction temperature	200	°C
T _{STG}	Storage temperature	-65 to +150	°C

^{1.} T_J = 150 °C

1.2 Thermal data

Table 3. Thermal data (1 msec - 10%)

Symbol	Parameter	Value	Unit
R _{thJC}	Junction - case thermal resistance	0.075	°C/W

Electrical characteristics STAC4932F

2 Electrical characteristics

 $T_{CASE} = +25 \, ^{\circ}C$

2.1 Static

Table 4. Static (per side)

Symbol	Test conditions			Min.	Тур.	Max.	Unit
V _{(BR)DSS} ⁽¹⁾	V _{GS} = 0 V	$I_{DS} = 100 \text{ mA}$		200	250		V
I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 100 V$				1	mA
I _{GSS}	V _{GS} = 20 V	$V_{DS} = 0 V$				250	nA
V_{TH}	I _D = 250 mA			2.0		4.0	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 10 A				3.6	V
G _{FS}	V _{DS} = 10 V	$I_D = 2.5 A$			6		S
C _{ISS}	V _{GS} = 0 V	V _{DS} = 100 V	f = 1 MHz		570		pF
C _{OSS}	V _{GS} = 0 V	V _{DS} = 100 V	f = 1 MHz		134		pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 100 V	f = 1 MHz		8		pF

^{1.} T_J = 150 °C

2.2 Dynamic

Table 5. Pulse / 1 mec - 10 %

Symbol	Test conditions		Тур.	Max.	Unit
P _{OUT}	V _{DD} = 100 V, I _{DQ} = 2 x 250 mA, f = 123 MHz	1000	1200	-	W
h _D	$V_{DD} = 100 \text{ V}, I_{DQ} = 2 \text{ x } 250 \text{ mA}, P_{OUT} = 1000 \text{ W}, f = 123 \text{ MHz}$		60	-	%
Gain	$V_{DD} = 100 \text{ V}, I_{DQ} = 2 \text{ x } 250 \text{ mA}, P_{OUT} = 1000 \text{ W},$ f = 123 MHz		26	-	dB

STAC4932F Impedance

3 Impedance

Figure 2. Current conventions

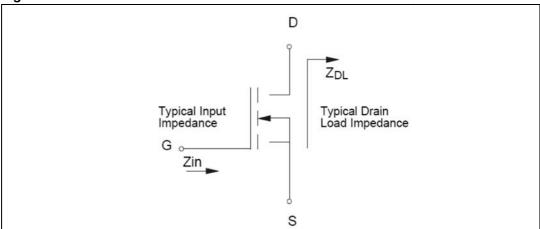


Table 6. Impedance data

Freq. (MHz)	Z _{IN} (Ω)	$Z_{DL}(\Omega)$
123 MHz (Pulse)	TBD	TBD

Note: Measured gate to gate and drain to drain, respectively.

4 Typical performances



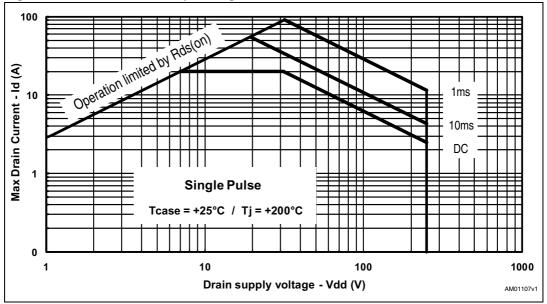


Figure 4. Transient thermal impedance

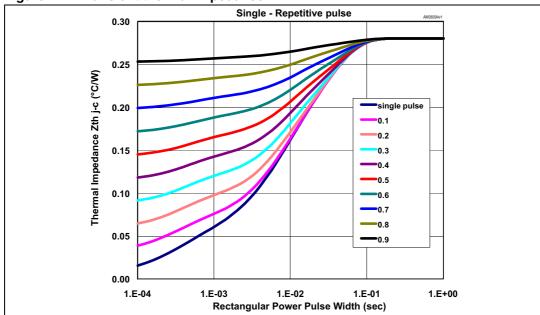


Figure 5. Transient thermal model

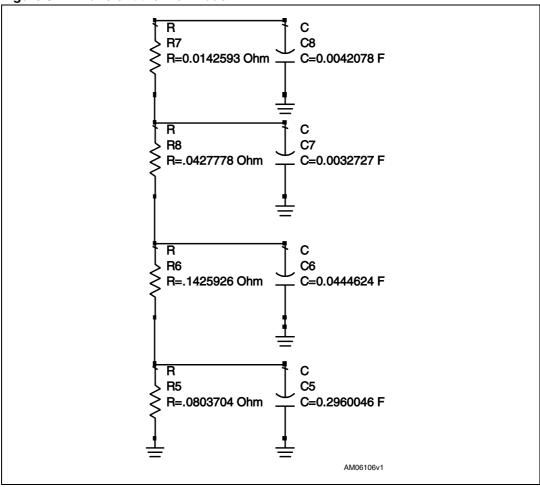
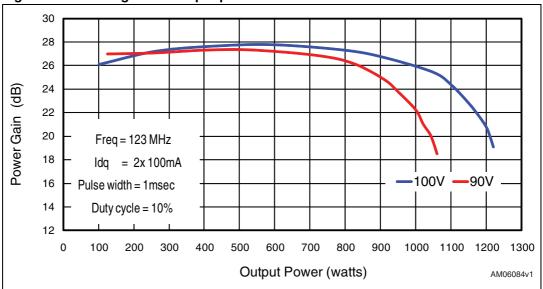


Figure 6. Power gain vs. output power



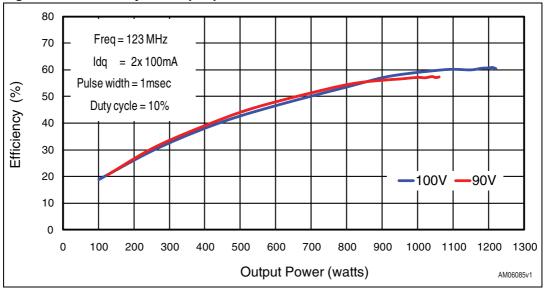


Figure 7. Efficiency vs. output power

5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 7. STAC244F package dimensions

Dim.	mm.		In	ch
Dilli.	Min	Max	Min	Max
А	5.10	5.59	200	220
A1	4.32	4.83	170	190
В	4.32	5.33	170	210
С	9.65	9.91	380	390
D	19.61	20.02	772	788
E	20.45	20.70	805	815
F	0.08	1.15	0.003	0.006
G	0.89	1.14	0.035	0.045
Н	1.45	1.70	0.057	0.067
I	3.18	4.32	0.125	0.170
J	9.27	9.53	0.365	0.375

10/12

→ 2XA1 - .07/1.8X45° 1 1 4X.020/0,51R. - 4X.005/0,13R. C J 4X.030/0,76 R 3 3 4XB - D E· 4XF G SEATING PLANE - 2 AM01112v1

Figure 8. Package dimensions

STAC4932F Revision history

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
22-Feb-2010	1	First release.
03-Aug-2010	2	Updated description on cover page and Table 3.
02-Sep-2010 3		Updated <i>Figure 8</i> . Added <i>Figure 3</i> , <i>4</i> and <i>5</i> .

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